

IN THE CLAIMS

1 (Currently Amended). A method comprising:

providing localized heating to a lithography mask made up of alternating layers of metal and silicon such that a metal silicide is formed to adjust for optical limitations in the mask formation process.

2 (Original). The method of claim 1 wherein providing localized heating to adjust for the proximity effect.

3 (Original). The method of claim 1 including providing localized heating to adjust for line end shortening.

4 (Original). The method of claim 1 wherein providing localized heating includes directing a laser beam to a localized region.

Claim 5 (Canceled).

6 (Original). The method of claim 1 including providing localized heating to an extreme ultraviolet lithography mask.

7 (Currently Amended). A lithography mask comprising:

a substrate; and

a stack over said substrate, said stack including alternate layers of metal and silicon, a silicide formed between at least one of said layers of metal and silicon, being thermally modified in a localized region.

8 (Original). The mask of claim 7 wherein said mask is an extreme ultraviolet lithography mask.

9 (Original). The mask of claim 7 wherein said mask is modified in a localized region to correct line end shortening.

10 (Original). The mask of claim 7 wherein said mask is modified in a localized region to reduce the proximity effect.

Claims 11-13 (Canceled).

14 (Original). An ultraviolet lithography mask comprising:
a substrate; and
a stack over said substrate, said stack including alternating layers of silicon and another material, and localized regions of silicide formed in a silicon layer.

15 (Original). The mask of claim 14 wherein said mask is modified in a localized region to correct line end shortening.

16 (Original). The mask of claim 14 wherein said mask is modified in a localized region to reduce the proximity effect.